

to permit a repair upon break of the data line, so that an effect of a throughput improvement can be obtain.

**In the Claims:**

Please **rewrite claims 1, 2, and 4** as follows:

Q<sup>10</sup>  
1. (Amended) A thin film transistor substrate in a liquid crystal display provided with a data line for applying a data signal, a gate line for applying a gate signal, and a pixel electrode for driving a liquid crystal cell, said substrate comprising:

a gate dummy pattern formed so as to extend vertically from the gate line and to overlap with the data line and the pixel electrode, the gate dummy pattern being integrated with the data line.

Q<sup>11</sup>  
2. (Amended) The thin film transistor substrate according to claim 1, wherein the gate dummy pattern is formed in such a manner to overlap with one side of the data line and the edge of the pixel electrode adjacent thereto.

Q<sup>12</sup>  
4. (Amended) The thin film transistor substrate according to claim 3, wherein the gate dummy pattern includes a recess connected to the gate line and formed to permit a repair.

Please **add claims 8-18** as follows:

--8. The thin film transistor substrate according to claim 1, wherein the gate dummy pattern is formed on the lower substrate having a gate-insulating layer at each side of the data line.

9. The thin-film transistor substrate according to claim 4, wherein the recess is provided at a cutting part for braking the gate line and the gate dummy pattern in such a manner as to not be overlapped with the data line.

10. A thin film transistor substrate in a liquid crystal display provided with a data line for applying a data signals, a gate line for applying a gate signal, and a pixel electrode for driving a liquid crystal cell, said substrate comprising:

a gate dummy pattern formed so as to extend vertically from the gate line and to overlap by from about 0.5-1  $\mu\text{m}$  with the data line and the pixel electrode, to thereby serve as a black matrix to shut off light leaked between said data line and said pixel electrode.

11. The thin film transistor substrate according to claim 10, wherein the gate dummy pattern is formed in such a manner to

overlap with one side or both sides of the data line and the edge of the pixel electrode adjacent thereto.

**12.** The thin film transistor substrate according to claim **11**, wherein the gate dummy pattern is used as a redundancy electrode for electrically connecting the gate line to the broken data line.

**13.** The thin film transistor substrate according to claim **12**, wherein the gate dummy pattern includes a hole connected to the gate line and formed to permit a repair.

**14.** The thin film transistor substrate according to claim **10**, wherein the gate dummy pattern is used as a black matrix.

**15.** The thin film transistor substrate according to claim **10**, further comprising:

a storage capacitor defined by a horizontal overlapping part between the gate line and the pixel electrode.

**16.** The thin film transistor substrate according to claim **14**, further comprising:

a protrusion formed in such a manner to overlap with the hole, thereby shutting off a light leaked between the gate dummy pattern and the gate line.

**17.** The thin film transistor substrate according to claim **10**, wherein the gate dummy pattern is formed on the lower substrate having a gate-insulating layer at each side of the data line.

**18.** The thin-film transistor substrate according to claim **10**, wherein the recess is provided at a cutting part for braking the gate line and the gate dummy pattern in such a manner as to not be overlapped with the data line. --

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